Absolute Maximum Ratings – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-20	V
Collector-Emitter Voltage	V_{CEO}	-20	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-2	A
Peak Pulse Collector Current	I_{CM}	-3	A
Base Current	I_B	-300	mA
Peak Base Current	I_{BM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

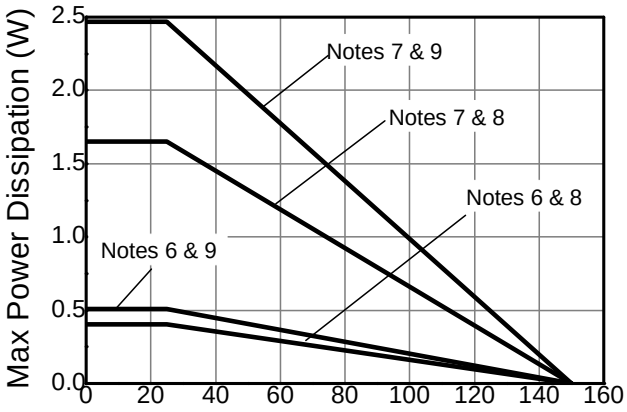
Characteristic		Symbol	Value	Unit
Power Dissipation	(Notes 6 & 8)	P_D	405	mW
	(Notes 6 & 9)		510	
	(Notes 7 & 8)		1650	
	(Notes 7 & 9)		2470	
Thermal Resistance, Junction to Ambient	(Notes 6 & 8)	$R_{\theta JA}$	308	°C/W
	(Notes 6 & 9)		245	
	(Notes 7 & 8)		76	
	(Notes 7 & 9)		51	
Thermal Resistance, Junction to Lead	(Note 10)	$R_{\theta JL}$	18	°C/W
Operating and Storage Temperature Range	—	T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 11)

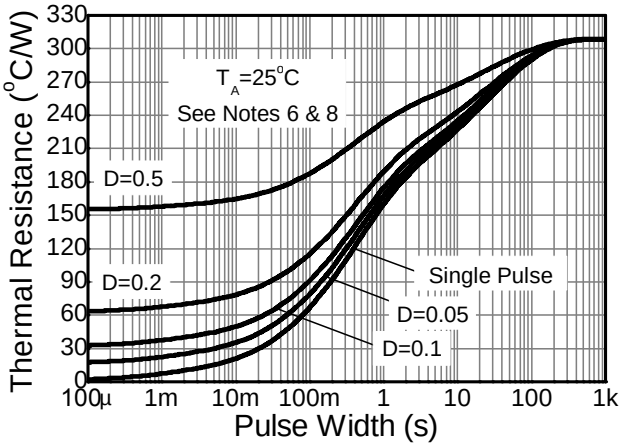
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	C

Notes:
6. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
7. Same as note (6), except the device is mounted with the collector pad on 28mm x 28mm (8cm^2) 2oz copper.
8. For a dual device with one active die.
9. For dual device with 2 active die running at equal power.
10. Thermal resistance from junction to solder-point (on the exposed collector pads).
11. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

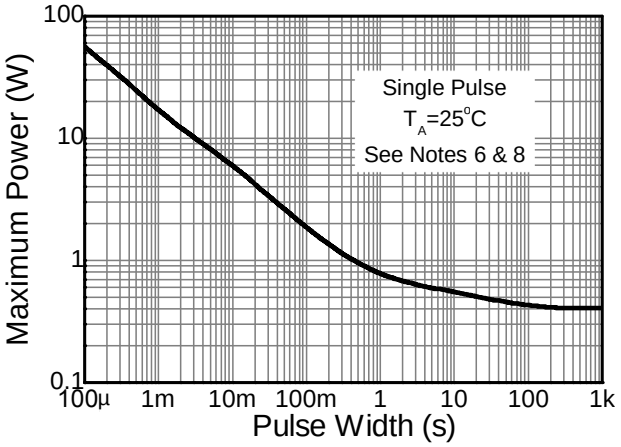
Thermal Characteristics and Derating Information



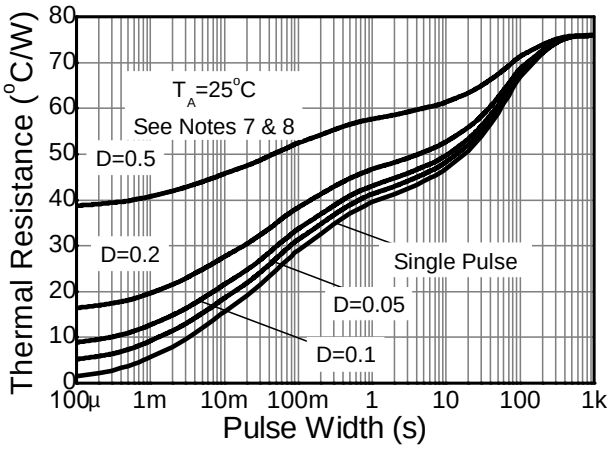
Derating Curve



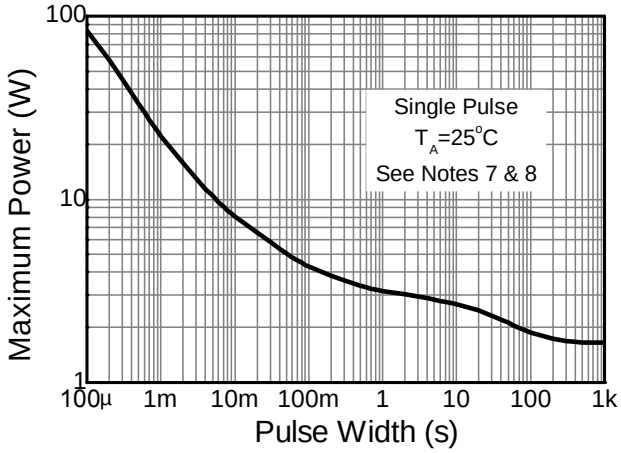
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



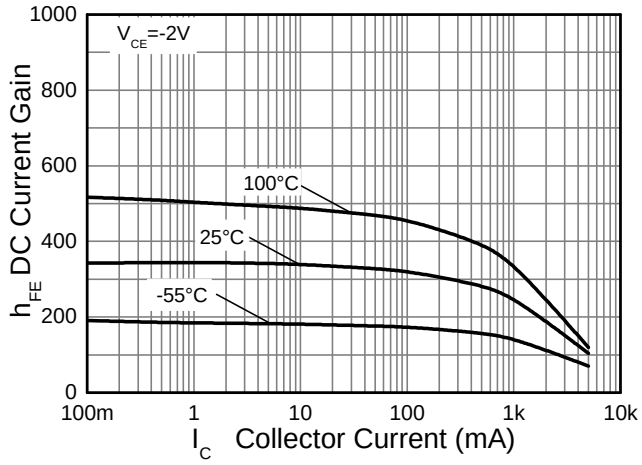
Pulse Power Dissipation

Electrical Characteristics – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

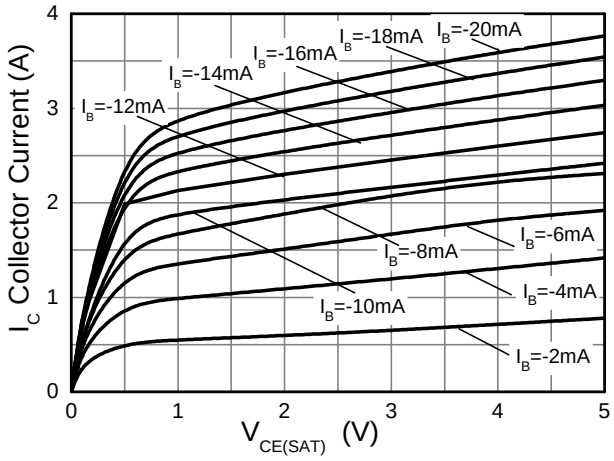
Characteristic	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-20	—	—	V	I_C = -100µA
Collector-Emitter Breakdown Voltage (Note 12)	BV_{CEO}	-20	—	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	—	—	V	I_E = -100µA
Collector-Base Cutoff Current	I_{CBO}	—	—	-100	nA	V_{CB} = -16V, I_E = 0
		—	—	-50	µA	V_{CB} = -16V, I_E = 0, T_A = +150°C
Emitter-Base Cutoff Current	I_{EBO}	—	—	-100	nA	V_{EB} = -5.6V, I_C = 0
DC Current Gain (Note 12)	h_{FE}	250	—	—	—	V_{CE} = -2V, I_C = -100mA
		210	—	—		V_{CE} = -2V, I_C = -500mA
		170	—	—		V_{CE} = -2V, I_C = -700mA
		160	—	—		V_{CE} = -2V, I_C = -1A
		100	—	—		V_{CE} = -2V, I_C = -2A
Collector-Emitter Saturation Voltage (Note 12)	$V_{CE(SAT)}$	—	—	-110	mV	I_C = -500mA, I_B = -50mA
		—	—	-220		I_C = -1A, I_B = -50mA
		—	—	-200		I_C = -0.7A, I_B = -7mA
		—	—	-390		I_C = -2A, I_B = -200mA
Equivalent On-Resistance (Note 12)	$R_{CE(SAT)}$	—	—	220	mΩ	I_E = -1A, I_B = -50mA
Base-Emitter Saturation Voltage (Note 12)	$V_{BE(SAT)}$	—	—	-1	V	I_C = -0.5A, I_B = -50mA
		—	—	-1.1		I_C = -1A, I_B = -50mA
		—	—	-1.25		I_C = -2A, I_B = -200mA
Base-Emitter Turn-on Voltage (Note 12)	$V_{BE(ON)}$	—	—	-0.9	V	V_{CE} = -2V, I_C = -0.5A
Turn-On Time	t_{ON}	—	60	—	ns	I_C = -1A, I_{B1} = -I_{B2} = 50mA; T_A = +25°C
Delay Time	t_D	—	10	—	ns	
Rise Time	t_R	—	50	—	ns	

Note: 12. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.

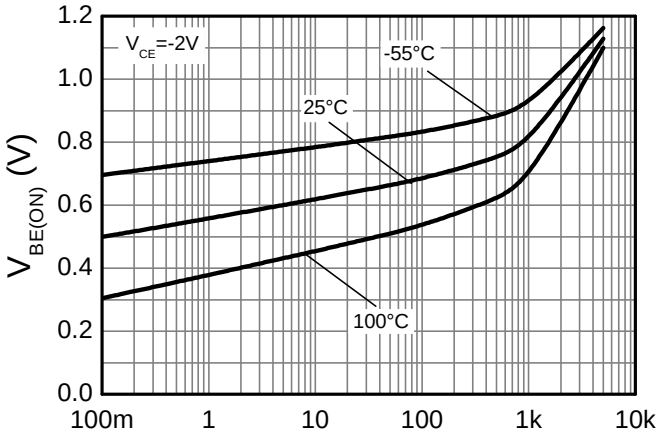
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



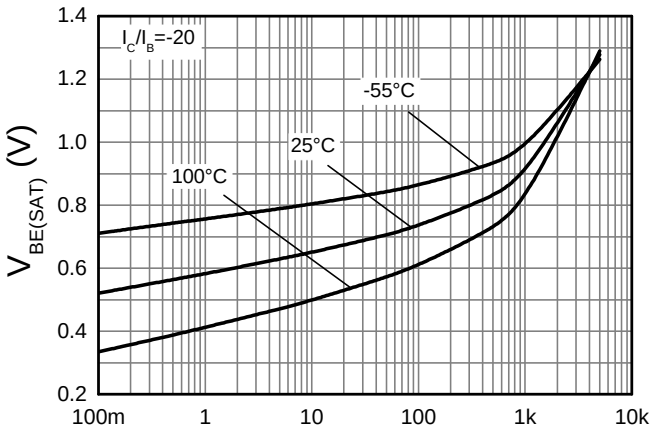
h_{FE} v Collector Current



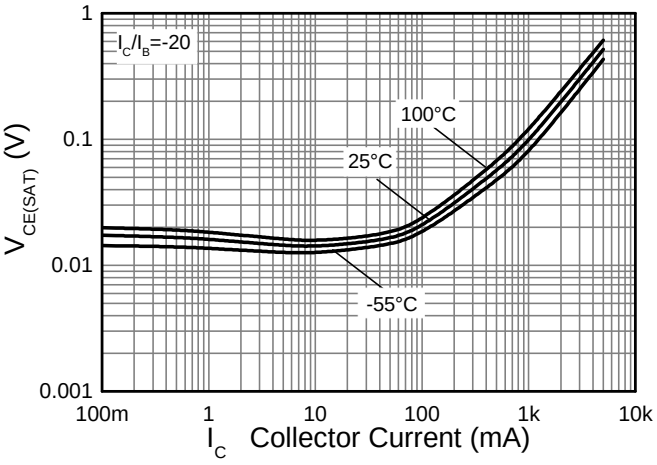
Collector Current v $V_{CE(SAT)}$



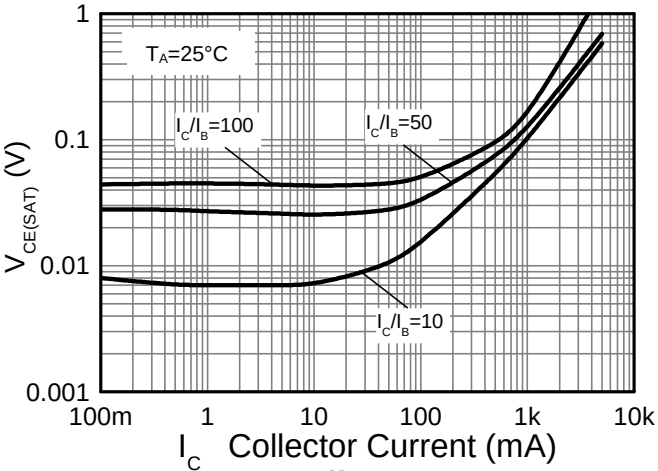
$V_{BE(ON)}$ v Collector Current



$V_{BE(SAT)}$ v Collector Current



$V_{CE(SAT)}$ v Collector Current

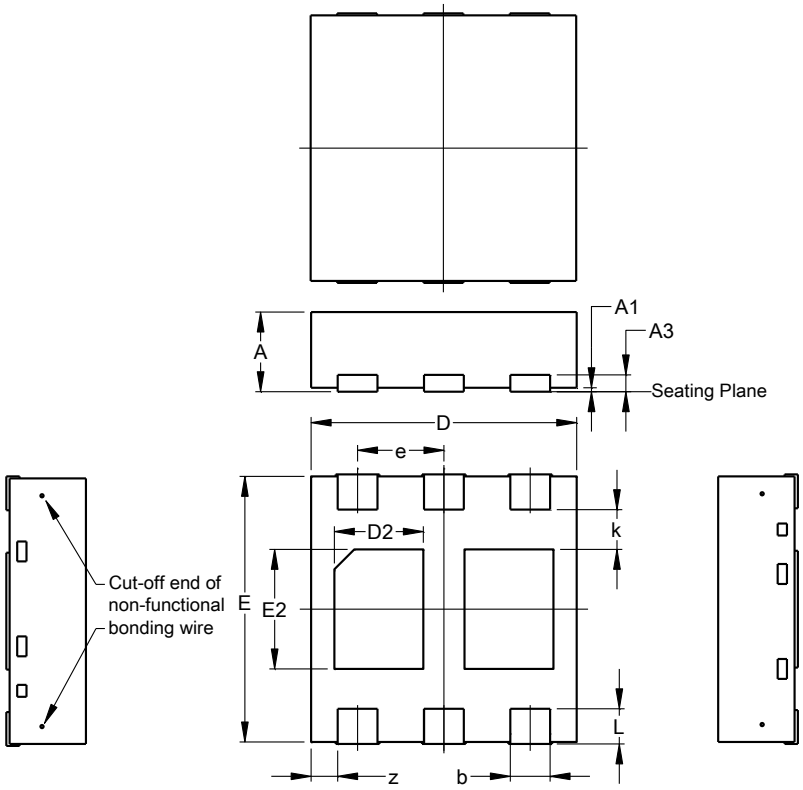


$V_{CE(SAT)}$ v Collector Current

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type A)

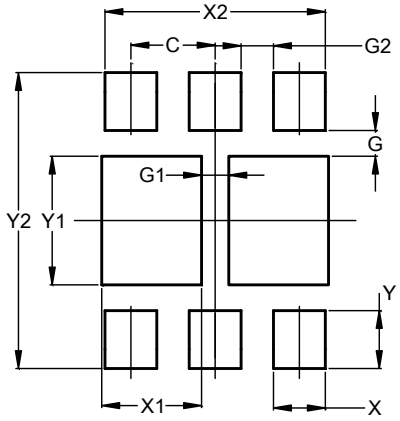


U-DFN2020-6 (SWP) (Type A)			
Dim	**Min**	**Max**	**Typ**
A	0.55	0.65	0.60
A1	0.00	0.05	0.03
A3	--	--	0.127
b	0.25	0.35	0.30
D	1.95	2.05	2.00
D2	0.57	0.77	0.67
E	1.95	2.05	2.00
E2	0.80	1.00	0.90
e	0.65BSC		
k	0.30BSC		
L	0.22	0.32	0.27
z	0.20BSC		
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type A)



Dimensions	Value (in mm)
C	0.650
G	0.200
G1	0.210
G2	0.250
X	0.400
X1	0.770
X2	1.700
Y	0.450
Y1	1.000
Y2	2.300

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